

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Previously presented): A semiconductor device comprising:

- a first insulating film formed over a semiconductor substrate;
- a second insulating film formed over the first insulating film;
- an interconnection structure buried in the first insulating film and in the second insulating film;
- a first dummy pattern of a first conducting layer buried in at least a surface side of the first insulating film near the interconnection structure; and
- a second dummy pattern formed of a second conducting layer buried in the second insulating film near the interconnection structure and connected to the first dummy pattern through a via portion, the second dummy pattern comprising a plurality of discrete patterns which are adjacent to each other and disposed at even intervals so as to make a pattern density of the second conducting layer substantially uniform in plane.

2. (Original): A semiconductor device according to claim 1, wherein

- the interconnection structure includes a first interconnection pattern buried in the first insulating film and formed of the first conducting layer, and a second interconnection pattern buried in the second insulating film, formed of the second conducting layer and connected to the first interconnection pattern through a via portion.

3. (Cancelled).

4. (Previously presented): A semiconductor device according to claim 1, wherein the via portion through which the second dummy pattern is connected to the first dummy pattern is formed in a part of the discrete patterns arranged near the interconnection structure.

5. (Previously presented): A semiconductor device according to claim 1, wherein the first dummy pattern comprises a plurality of discrete patterns periodically formed so as to make a pattern density of the first conducting layer substantially uniform in plane.

6. (Original): A semiconductor device according to claim 1, wherein the first conducting layer and the second conducting layer are formed of a conducting material mainly based on copper.

7. (Previously presented): A semiconductor device according to claim 1, wherein the first insulating film and the second insulating film are formed of films based mainly on different insulating materials with each other.

8. (Original): A semiconductor device according to claim 7, wherein the first insulating film is mainly formed of a polyallyl ether resin film, and the second insulating film is mainly formed of a organosilicate glass film.

Amendment under 37 C.F.R. §1.116(b)(1)

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9. (Original): A semiconductor device according to claim 2, wherein
the via portion through which the second interconnection pattern is connected to the first
interconnection pattern has a groove-shaped pattern.

10. (Original): A semiconductor device according to claim 1, wherein
the interconnection structure is a guard ring, an inductor or a pad.

11-18. (Cancelled).